

ABSTRACT

A process of forming a conductive layer on a wafer is provided. A front surface and an edge surface of the wafer are coated with a seed layer. Further, the edge surface includes a back edge surface, a bevel surface and a front edge surface. During the process, the seed layer is removed from the back edge surface and the bevel surface using an etching process. Next, the conductive layer is formed by depositing a conductive material onto the remaining seed layer which coats the front edge surface and the front surface of the wafer. A part of the conductive layer which is on the front edge surface is then removed using another etching process.